L Number	Hits	Search Text	DB	Time stamp
1	444	(shallow adj junction) and (deep adj	USPAT;	2004/10/25
·		junction)	US-PGPUB;	09:43
		·	EPO; JPO;	00.40
			DERWENT;	
			IBM_TDB	
2	. 180	(shallow adj junction) with (deep adj	USPAT;	2004/10/25
-		junction)	US-PGPUB;	09:43
		, and the same of	EPO; JPO;	00.40
			DERWENT;	
			IBM_TDB	
3	17	((shallow adj junction) with (deep adj	USPAT;	2004/10/25
•	••	junction)).clm.	US-PGPUB;	09:44
		junction)).ciiii.	EPO; JPO;	03.44
			DERWENT;	
			IBM_TDB	
4	0	((shallow adj junction) with (deep adj	USPAT;	2004/10/25
7	•	junction)).clm. and (laser near (anneal or	*	
		annealing or annealed)).clm.	US-PGPUB;	09:45
		annealing or annealed)).cim.	EPO; JPO;	
			DERWENT;	
5	4	((aballam adi imadian) midh (daan adi	IBM_TDB	2004/40/05
3	1	((shallow adj junction) with (deep adj	USPAT;	2004/10/25
		junction)).clm. and (laser near (anneal or	US-PGPUB;	09:45
		annealing or annealed))	EPO; JPO;	
			DERWENT;	
	4	(fab. 11	IBM_TDB	
6	1	((shallow adj junction) with (deep adj	USPAT;	2004/10/25
		junction)).clm. and (amorphize or	US-PGPUB;	09:46
		amorphizing or amorphized or	EPO; JPO;	
		amorphization).clm.	DERWENT;	
_	4	// L II . II	IBM_TDB	
7	1	((shallow adj junction) and (deep adj	USPAT;	2004/10/25
		junction)).clm. and (amorphize or	US-PGPUB;	09:46
		amorphizing or amorphized or	EPO; JPO;	
		amorphization).clm.	DERWENT;	
.	_	(/akallana / 12 tana	IBM_TDB	
8	1	((shallow adj junction) and (deep adj	USPAT;	2004/10/25
		junction)).ti,ab,clm. and (amorphize or	US-PGPUB;	09:46
		amorphizing or amorphized or	EPO; JPO;	
		amorphization).clm.	DERWENT;	
_	4		IBM_TDB	
9	1	((shallow adj junction) and (deep adj	USPAT;	2004/10/25
		junction)).ti,ab,clm. and (amorphize or	US-PGPUB;	09:46
		amorphizing or amorphized or	EPO; JPO;	
	·	amorphization).ti,ab,clm.	DERWENT;	
40			IBM_TDB	
10	2	((shallow adj junction) and (deep adj	USPAT;	2004/10/25
		junction)).ti,ab,clm. and (amorphize or	US-PGPUB;	09:47
		amorphizing or amorphized or	EPO; JPO;	
		amorphization)	DERWENT;	
			IBM_TDB	

11	25	(junction same (amorphize or amorphizing	USPAT;	2004/10/25
		or amorphized or amorphiation)).clm.	US-PGPUB;	09:48
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
12	10	(junction same (amorphize or amorphizing	USPAT;	2004/10/25
		or amorphized or amorphiation) same gate	US-PGPUB;	09:48
		same source same drain).clm.	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
13	1	(junction same (amorphize or amorphizing	USPAT;	2004/10/25
		or amorphized or amorphiation) same gate	US-PGPUB;	09:48
		same source same drain same	EPO; JPO;	•
		capacitance).clm.	DERWENT;	•
			IBM_TDB	
14	1	(junction same (amorphize or amorphizing	USPAT;	2004/10/25
		or amorphized or amorphiation) same gate	US-PGPUB;	09:48
	,	same source same drain same capacitance) .	EPO; JPO;	
			DERWENT;	
4.5			IBM_TDB	
15	23	(junction same (amorphize or amorphizing	USPAT;	2004/10/25
		or amorphized or amorphiation) same gate	US-PGPUB;	09:48
		same source same drain).ti,ab,clm.	EPO; JPO;	
			DERWENT;	
16	6	//www.diam.com.c./cmacom.bin.c.macom.bini.c.	IBM_TDB	2004/40/05
16	•	(junction same (amorphize or amorphizing	USPAT;	2004/10/25
		or amorphized or amorphiation) same gate same source same drain).ti,ab,clm. and	US-PGPUB;	09:49
		capacitance	EPO; JPO; DERWENT;	1
		capacitance	IBM_TDB	
17	3	(junction same (amorphize or amorphizing	USPAT;	2004/10/25
''		or amorphized or amorphiation) same gate	US-PGPUB;	09:50
		same source same drain).ti,ab,clm. and	EPO; JPO;	03.30
		capacitance and laser	DERWENT;	
			IBM_TDB	
18	3	(junction same (amorphize or amorphizing	USPAT;	2004/10/25
		or amorphized or amorphiation) same gate	US-PGPUB;	09:51
		same source same drain).ti,ab,clm. and	EPO; JPO;	
		capacitance and laser and (ion adj (implant	DERWENT:	
	1	or implanting or implanted or implantation))	IBM_TDB	
19	2	(junction same (amorphize or amorphizing	USPAT;	2004/10/25
		or amorphized or amorphiation) same gate	US-PGPUB;	09:52
		same source same drain).ti,ab,clm. and	EPO; JPO;	
		capacitance and laser and (ion adj (implant	DERWENT;	
1		or implanting or implanted or implantation))	IBM_TDB	
		and ((shallow or deep) adj junction)	7	
20	2	(junction same (amorphize or amorphizing	USPAT;	2004/10/25
		or amorphized or amorphiation) same gate	US-PGPUB;	09:52
		same source same drain).ti,ab,clm. and	EPO; JPO;	
		capacitance and laser and (ion adj (implant	DERWENT;	
		or implanting or implanted or implantation))	IBM_TDB	
		and ((shallow or deep) adj junction) and		
		crystal		

24	2	//	HCDAT.	2004/40/25
21	2	(junction same (amorphize or amorphizing	USPAT;	2004/10/25
		or amorphized or amorphiation) same gate	US-PGPUB;	09:53
		same source same drain).ti,ab,clm. and	EPO; JPO;	
		capacitance and laser and (ion adj (implant	DERWENT;	
		or implanting or implanted or implantation))	IBM_TDB	
		and ((shallow or deep) adj junction) and		
200		(single adj crystal)		
22	2	(junction and (amorphize or amorphizing or	USPAT;	2004/10/25
		amorphized or amorphiation) and gate and	US-PGPUB;	09:54
		source and drain).ti,ab,clm. and	EPO; JPO;	
		capacitance and laser and (ion adj (implant	DERWENT;	
		or implanting or implanted or implantation))	IBM_TDB	
		and ((shallow or deep) adj junction) and		
		(single adj crystal)		
23	16	(junction and (amorphize or amorphizing or	USPAT;	2004/10/25
		amorphized or amorphiation) and gate and	US-PGPUB;	09:58
		source and drain) and capacitance and	EPO; JPO;	
		laser and (ion adj (implant or implanting or	DERWENT;	•
		implanted or implantation)) and ((shallow or	IBM_TDB	
		deep) adj junction) and (single adj crystal)	15155	
24	2	((junction and (amorphize or amorphizing or	USPAT;	2004/10/25
	_	amorphized or amorphiation) and gate and	1 · · ·	
		· · · · ·	US-PGPUB;	10:01
		source and drain) and capacitance and	EPO; JPO;	
		laser and (ion adj (implant or implanting or	DERWENT;	
		implanted or implantation)) and ((shallow or	IBM_TDB	
		deep) adj junction) and (single adj crystal))		
		and (sharp adj (dopant or impurity) adj		
	_ 1	profile)		
25	4	((junction and (amorphize or amorphizing or	USPAT;	2004/10/25
		amorphized or amorphiation) and gate and	US-PGPUB;	10:04
		source and drain) and capacitance and	EPO; JPO;	
		laser and (ion adj (implant or implanting or	DERWENT;	
		implanted or implantation)) and ((shallow or	IBM_TDB	
		deep) adj junction) and (single adj crystal))		
		and ((amorphize or amorphized or		
		amorphizing or amorphization) near5		
		(dopant or impurity))		
26	1	((junction and (amorphize or amorphizing or	USPAT;	2004/10/25
		amorphized or amorphiation) and gate and	US-PGPUB;	10:04
		source and drain) and capacitance and	EPO; JPO;	
		laser and (ion adj (implant or implanting or	DERWENT;	
		implanted or implantation)) and ((shallow or	IBM_TDB	
		deep) adj junction) and (single adj crystal))		
		and ((amorphize or amorphized or		
		amorphizing or amorphization) near5		
}		(dopant or impurity) near5 junction)		
		(aspant of impurity) nears junction)		